SEMICONDUCTORS

## ZXTN19055DZ

55V, SOT89, NPN medium power transistor

## Summary

$B V_{\text {CEX }}>150 \mathrm{~V}$
$B V_{\text {CEO }}>55 \mathrm{~V}$
$I_{\text {(cont) }}=6 \mathrm{~A}$

$\mathrm{V}_{\mathrm{CE}(\text { sat })}<60 \mathrm{mV}$ @ 1A
$R_{\text {CE(sat) }}=\mathbf{2 8 m} \Omega$
$\mathrm{P}_{\mathrm{D}}=2.1 \mathrm{~W}$

## Description

Packaged in the SOT89 outline this low saturation 55V NPN transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

## Feature

- Extremely low equivalent on-resistance of $28 \mathrm{~m} \Omega$
- 6 Amps continuous current
- Up to 10 amps peak current
- Very low saturation voltages
- Excellent $\mathrm{h}_{\text {FE }}$ characteristics up to 10 amps
- 150V Forward blocking voltage


## Applications

- Emergency lighting circuits
- Motor driving (including DC fans)

- Solenoid, relay and actuator drivers
- DC modules
- Backlight inverters


## Ordering information

| Device | Reel size <br> (inches) | Tape width <br> $(\mathbf{m m})$ | Quantity per reel |
| :--- | :---: | :---: | :---: |
| ZXTN19055DZTA | 7 | 12 | 1000 |

## Device marking

S75

## ZXTN19055DZ

## Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Collector-base voltage | $\mathrm{V}_{\mathrm{CBO}}$ | 150 | V |
| Collector-emitter voltage (forward blocking voltage) | $\mathrm{V}_{\mathrm{CEX}}$ | 150 | V |
| Collector-emitter voltage (base open) | $\mathrm{V}_{\text {CEO }}$ | 55 | V |
| Emitter-base voltage | $\mathrm{V}_{\text {EBO }}$ | 7 | V |
| Continuous collector current ${ }^{(\mathrm{b})}$ | $\mathrm{I}_{\mathrm{C}}$ | 6 | A |
| Peak pulse current | $\mathrm{I}_{\mathrm{CM}}$ | 10 | A |
| Power dissipation at $\mathrm{T}_{\text {amb }}=\mathbf{2 5}^{\circ} \mathrm{C}^{\text {(a) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 1.5 | W |
| Linear derating factor |  | 12 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Power dissipation at $\mathrm{T}_{\mathrm{amb}}=\mathbf{2 5}^{\circ} \mathrm{C}^{\text {(b) }}$ | $\mathrm{P}_{\mathrm{D}}$ | 2.1 | W |
| Linear derating factor |  | 16.8 | $\mathrm{~mW} /{ }^{\circ} \mathrm{C}$ |
| Operating and storage temperature range | $\mathrm{T}_{\mathrm{j}}, \mathrm{T}_{\text {stg }}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

## Thermal resistance

| Parameter | Symbol | Limit | Unit |
| :--- | :---: | :---: | :---: |
| Junction to ambient $^{(\mathrm{a})}$ | $\mathrm{R}_{\Theta J A}$ | 83 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |
| Junction to ambient $^{(\mathrm{b})}$ | $\mathrm{R}_{\Theta J A}$ | 59 | ${ }^{\circ} \mathrm{C} / \mathrm{W}$ |

## NOTES:

(a) For a device surface mounted on $25 \mathrm{~mm} \times 25 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions.
(b) For a device surface mounted on $50 \mathrm{~mm} \times 50 \mathrm{~mm} \times 1.6 \mathrm{~mm}$ FR4 PCB with high coverage of single sided 10 copper, in still air conditions.

## ZXTN19055DZ

## Characteristics




Transient Thermal Impedance




## ZXTN19055DZ

Electrical characteristics (at $\mathrm{T}_{\mathrm{amb}}=\mathbf{2 5}{ }^{\circ} \mathrm{C}$ unless otherwise stated)

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Conditions |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| Collector-base breakdown voltage | $\mathrm{BV}_{\mathrm{CBO}}$ | 150 | 200 |  | V | $\mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}$ |
| Collector-emitter breakdown voltage (forward blocking) | $\mathrm{BV}_{\text {CEX }}$ | 150 | 200 |  | V | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{R}_{\mathrm{BE}}<1 \mathrm{k} \Omega \text { or } \\ & -1 \mathrm{~V}<\mathrm{V}_{\mathrm{BE}}<+0.25 \mathrm{~V} \end{aligned}$ |
| Collector-emitter breakdown voltage (base open) | $\mathrm{BV}_{\text {CEO }}$ | 55 | 75 |  | V | $\mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}^{(*)}$ |
| Emitter-base breakdown voltage | $\mathrm{BV}_{\mathrm{EBO}}$ | 7 | 8.1 |  | V | $\mathrm{IE}=100 \mathrm{~mA}$ |
| Collector-base cut-off current | $\mathrm{I}_{\text {CBO }}$ |  | <1 | $\begin{aligned} & 50 \\ & 20 \end{aligned}$ | nA $\mu \mathrm{A}$ | $\begin{aligned} & \mathrm{V}_{\mathrm{CB}}=120 \mathrm{~V} \\ & \mathrm{~V}_{\mathrm{CB}}=120 \mathrm{~V}, \mathrm{~T}_{\mathrm{amb}}=100^{\circ} \mathrm{C} \end{aligned}$ |
| Collector-emitter cut-off current | ${ }^{\text {I CEX }}$ |  | <1 | 100 | nA | $\begin{aligned} & \mathrm{V}_{\mathrm{CE}}=120 \mathrm{~V} ; \mathrm{R}_{\mathrm{BE}}<1 \mathrm{k} \Omega \text { or } \\ & -1 \mathrm{~V}<\mathrm{V}_{\mathrm{BE}}<0.25 \mathrm{~V} \end{aligned}$ |
| Emitter cut-off current | IEBO |  | <1 | 50 | nA | $\mathrm{V}_{\mathrm{EB}}=5.6 \mathrm{~V}$ |
| Collector-emitter saturation voltage | $\mathrm{V}_{\mathrm{CE} \text { (sat) }}$ |  | $\begin{gathered} 25 \\ 45 \\ 40 \\ 200 \\ 110 \\ 140 \\ 170 \end{gathered}$ | 40 70 60 350 140 200 250 | mV <br> mV <br> mV <br> mV <br> mV <br> mV <br> mV | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=0.5 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}^{\left({ }^{(*)}\right.} \\ & \mathrm{I}_{\mathrm{C}}=1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=50 \mathrm{~mA}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=1 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=100 \mathrm{~mA}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=2 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=20 \mathrm{~mA}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=2 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=40 \mathrm{~mA}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=4 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=200 \mathrm{~mA}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=6 \mathrm{~A}, \mathrm{I}_{\mathrm{B}}=600 \mathrm{~mA}^{(*)} \end{aligned}$ |
| Base-emitter saturation voltage | $\mathrm{V}_{\mathrm{BE} \text { (sat) }}$ |  | $\begin{gathered} \hline 800 \\ 1000 \end{gathered}$ | $\begin{gathered} 900 \\ 1150 \end{gathered}$ | $\begin{aligned} & \mathrm{mV} \\ & \mathrm{mV} \end{aligned}$ | $\begin{aligned} & I_{C}=2 A, I_{B}=20 m A^{(*)} \\ & I_{C}=6 A, I_{B}=600 m A^{(*)} \end{aligned}$ |
| Base-emitter turn-on voltage | $\mathrm{V}_{\text {BE(on) }}$ |  | $\begin{aligned} & 760 \\ & 900 \end{aligned}$ | $\begin{gathered} 900 \\ 1050 \end{gathered}$ | $\begin{aligned} & \mathrm{mV} \\ & \mathrm{mV} \end{aligned}$ | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=2 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=6 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \end{aligned}$ |
| Static forward current transfer ratio | $\mathrm{h}_{\mathrm{FE}}$ | $\begin{gathered} 250 \\ 250 \\ 180 \\ 30 \end{gathered}$ | $\begin{gathered} 400 \\ 400 \\ 300 \\ 50 \\ 20 \end{gathered}$ | 700 |  | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=10 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=1 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=2 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=6 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \\ & \mathrm{I}_{\mathrm{C}}=10 \mathrm{~A}, \mathrm{~V}_{\mathrm{CE}}=2 \mathrm{~V}^{(*)} \end{aligned}$ |
| Transition frequency | $\mathrm{f}_{\mathrm{T}}$ | 140 | 200 |  | MHz | $\begin{aligned} & \mathrm{I}_{\mathrm{C}}=100 \mathrm{~mA}, \mathrm{~V}_{\mathrm{CE}}=10 \mathrm{~V} \\ & \mathrm{f}=50 \mathrm{MHz} \end{aligned}$ |
| Output capacitance | $\mathrm{C}_{\text {OBO }}$ |  | 21.2 | 30 | pF | $\mathrm{V}_{\mathrm{CB}}=10 \mathrm{~V}, \mathrm{f}=1 \mathrm{MHz}$ |
| Delay time | $\mathrm{t}_{\mathrm{d}}$ |  | 13.8 |  |  | $\mathrm{V}_{C C}=10 \mathrm{~V}$, |
| Rise time | $\mathrm{t}_{\mathrm{r}}$ |  | 21.9 |  |  | $\mathrm{I}_{\mathrm{C}}=1 \mathrm{~A}$, |
| Storage time | $\mathrm{t}_{\mathrm{s}}$ |  | 546 |  |  | $\mathrm{I}_{\mathrm{B} 1}=\mathrm{I}_{\mathrm{B} 2}=100 \mathrm{~m}$ |
| Fall time | $\mathrm{t}_{\mathrm{f}}$ |  | 106 |  |  |  |

NOTES:
(*) Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2 \%$.

## ZXTN19055DZ

## Typical characteristics



## ZXTN19055DZ

## Package outline - SOT89



| DIM | Millimeters |  | Inches |  | DIM | Millimeters |  | Inches |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | Min | Max | Min | Max |  | Min | Max | Min | Max |
| A | 1.40 | 1.60 | 0.550 | 0.630 | E1 | 2.13 | 2.29 | 0.084 | 0.090 |
| B | 0.44 | 0.56 | 0.017 | 0.022 | e | 1.50 BSC |  | 0.059 BSC |  |
| B1 | 0.36 | 0.48 | 0.014 | 0.019 | e1 | 3.00 BSC |  | 0.118 BSC |  |
| C | 0.35 | 0.44 | 0.014 | 0.019 | H | 3.94 | 4.25 | 0.155 | 0.167 |
| D | 4.40 | 4.60 | 0.173 | 0.181 | L | 0.89 | 1.20 | 0.155 | 0.167 |
| E | 2.29 | 2.60 | 0.090 | 0.102 |  | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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